

FET Transistor

N-Channel — Enhancement

MAXIMUM RATINGS

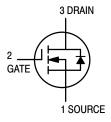
Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	Vdc
Drain–Gate Voltage ($R_{GS} = 1 \text{ M}\Omega$)	V_{DGR}	60	Vdc
Gate–Source Voltage – Continuous – Non–repetitive (t _p ≤ 50 μs)	V _{GS} V _{GSM}	± 20 ± 40	Vdc Vpk
Drain Current Continuous Pulsed	I _D	190 1000	mAdc
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	400 3.2	mW mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

CASE 29–11, STYLE 22 TO–92 (TO–226AA)

VN0610LL

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	312.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/16" from case for 10 seconds	TL	300	°C



ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Drain–Source Breakdown Voltage $(V_{GS} = 0, I_D = 100 \mu A)$	V _{(BR)DSS}	60	_	Vdc	
Zero Gate Voltage Drain Current $(V_{DS} = 48 \text{ Vdc}, V_{GS} = 0)$ $(V_{DS} = 48 \text{ Vdc}, V_{GS} = 0, T_J = 125^{\circ}\text{C})$	I _{DSS}		10 500	μAdc	
Gate-Body Leakage Current, Forward (V _{GSF} = 30 V, V _{DS} = 0)	I _{GSSF}	_	-100	nAdc	
ON CHARACTERISTICS ⁽¹⁾					
Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = 1.0$ mA)	V _{GS(th)}	0.8	2.5	Vdc	
Chatia Dunia Causas On Basistana	_			0	

Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = 1.0 \text{ mA}$)		8.0	2.5	Vdc
Static Drain–Source On–Resistance	r _{DS(on)}			Ω
$(V_{GS} = 10 \text{ V}, I_D = 500 \text{ mA})$		_	5.0	
$(V_{GS} = 10 \text{ V}, I_D = 500 \text{ mA}, T_C = 125^{\circ}\text{C})$			9.0	
Drain-Source On-Voltage	V _{DS(on)}			Vdc
$(V_{GS} = 5.0 \text{ V}, I_D = 200 \text{ mA})$, ,	_	1.5	
$(V_{GS} = 10 \text{ V}, I_D = 500 \text{ mA})$		_	2.5	
On–State Drain Current ($V_{GS} = 10 \text{ V}, V_{DS} \ge 2.0 \text{ V}_{DS(on)}$)	I _{D(on)}	750	_	mAdc
Forward Transconductance ($V_{DS} \ge 2.0 V_{DS(on)}$, $I_D = 500 \text{ mA}$)	9fs	100	_	μmhos

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

	Symbol	Min	Max	Unit	
DYNAMIC CHARACTERISTI	cs				•
Input Capacitance		C _{iss}	_	60	pF
Output Capacitance	$(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0,$ f = 1.0 MHz)	C _{oss}	_	25	
Reverse Transfer Capacitance	· ···· ···-,	C _{rss}	_	5.0	
SWITCHING CHARACTERIS	TICS ⁽¹⁾				
Turn-On Delay Time	(V _{DD} = 15 Vdc, I _D = 600 mA,	t _{on}	_	10	ns
Turn-Off Delay Time	$R_{gen} = 25 \Omega$, $R_L = 23 \Omega$)	t _{off}	_	10	

^{1.} Pulse Test: Pulse Width \leq 300 ms, Duty Cycle \leq 10%.

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RESISTIVE SWITCHING

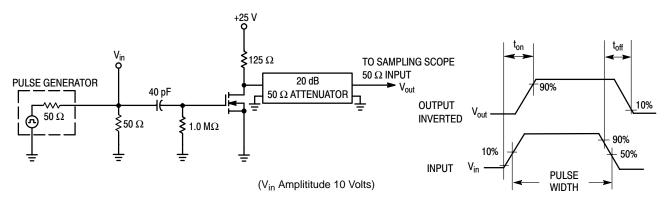


Figure 1. Switching Test Circuit

Figure 2. Switching Waveforms

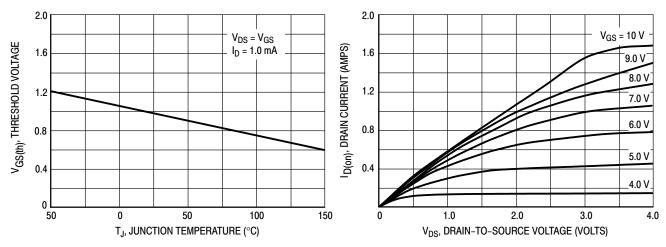


Figure 3. V_{GS(th)} Normalized versus Temperature

Figure 4. On-Region Characteristics

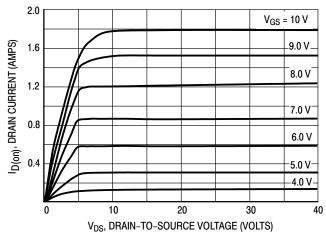


Figure 5. Output Characteristics

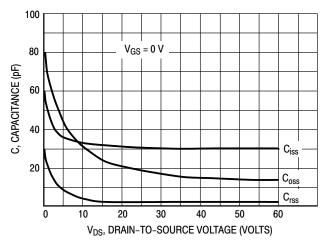
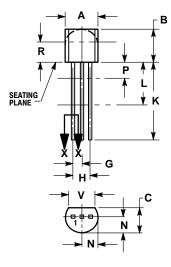


Figure 6. Capacitance versus Drain-To-Source Voltage

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PACKAGE DIMENSIONS

TO-92 (TO-226AA) **CASE 29-11 ISSUE AL**





STYLE 22: PIN 1.

SOURCE 2. GATE DRAIN

NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R
 IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

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